

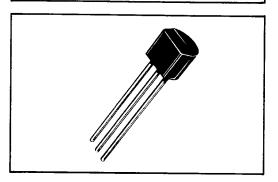
# MTS102 MTS103 MTS105

## SILICON TEMPERATURE SENSORS

...designed for temperature sensing applications in automotive, consumer, and industrial products requiring low cost and high accuracy.

- Precise Temperature Accuracy Over Extreme Temperature MTS102: ±2°C from ~40°C to +150°C
- Precise Temperature Coefficient
- Fast Thermal Time Constant
  - 3 Seconds Liquid 8 Seconds — Air
- Linear VBE versus Temperature Curve Relationship

## SILICON TEMPERATURE SENSORS



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	MILLIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.32	5.33	0.170	0.210	
В	4.44	5.21	0.175	0.205	
C	3.18	4.19	0.125	0.165	
D	0.41	0.56	0.016	0.022	
F	0.41	0.48	0.016	0.019	
G	1.14	1.40	0.045	0.055	
Н	-	2.54	-	0.100	
J	2.41	2.67	0.095	0.105	
K	12.70	_	0.500	_	
L	6.35		0.250	- `	
N	2.03	2.92	0.080	0.115	
P	2.92	_	0.115		
R	3.43	_	0.135		
S	0.36	0.41	0.014	0.016	

All JEDEC dimensions and notes apply.

CASE 29-02

TO-92

## **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	40	Vdc
Emitter-Base Voltage	VEB	4.0	Vdc
Collector Current — Continuous*	lс	100	mAdc
Total Power Dissipation @ T <sub>A</sub> = 25 <sup>0</sup> C Derate Above 25 <sup>0</sup> C	PD	625 5.0	mW mW/ <sup>O</sup> C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	~55 to +150	°С

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

<sup>\*</sup>See Note 5, page 2.

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

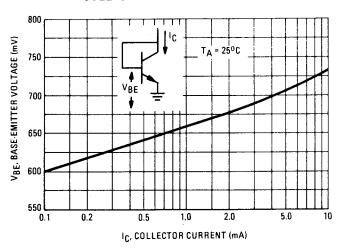
Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage (I <sub>C</sub> = 1.0 mAdc, I <sub>B</sub> = 0)		BVCEO	40	-	-	Vdc
Emitter-Base Breakdown Voltage $(I_E = 100 \mu\text{Adc}, I_C = 0)$		BVEBO	4.0	_		Vdc
Collector Cutoff Current (V <sub>CE</sub> = 30 Vdc, I <sub>E</sub> = 0)		ICEO	-	-	100	nAdc
Base-Emitter Voltage I <sub>C</sub> = 0.1 mA		V <sub>BE</sub>	580	600	620	mV
Base-Emitter Voltage Matching, Note 1 (IC = 0.1 mA)		ΔVBE				m∨
	MTS102		-	-	± 3.0	İ
	MTS103		-	-	± 4.0	
	MTS105			-	± 7.0	
Temperature Accuracy, Note 2 $(T1 = -40^{\circ}C, T2 = +150^{\circ}C)$		ΔΤ				°C
	MTS102		_	-	± 2.0	
	MTS103		-	-	± 3.0	
	MTS105	<b>I</b>	-	-	± 5.0	
Temperature Coefficient, Notes 3 and 4 (VBE = 600 mV, IC = 0.1 mA)		тс	-2.26	~2.25	-2.24	mV/ <sup>o</sup> C
Thermal Time Constant		$ au_{TH}$				s
Flowing Liquid			_	3.0	_	
Flowing Air				8.0	_	
Dependence of TC on V <sub>BE</sub> @ 25 <sup>o</sup> C (Note 4, Figure 2)		ΔΤC/ΔVΒΕ		0.0033	_	mV/ <sup>o</sup> C mV

#### NOTES

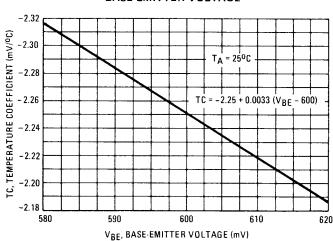
- 1. For orders of 1000 pieces of less, devices will be matched in a single group. For larger orders, devices will be supplied in groups of 1000 minimum per group. All devices within any one group will be matched for VBE to the tolerance identified in the electrical characteristics table. All groups will be labeled with the nominal VBE value for that group.
- 2. All devices within an individual group, as described in Note 1, will track within the specified temperature accuracy. Includes variations in TC,  $V_{BE}$ , and non-linearity in the range -40 to +150°C. Non-linearity is typically less than  $\pm$  1°C in this range.
- 3. The TC as defined by a least-square linear regression for V<sub>BE</sub> versus temperature over the range -40 to +150°C for a nominal V<sub>BE</sub> of 600 mV at 25°C. For other nominal V<sub>BE</sub> values the value of the TC must be adjusted for the dependence of the TC on V<sub>BE</sub> (see Note 4).
- 4. For nominal VBE at 25°C other than 600 mV, the TC must be corrected using the equation TC = -2.25 + 0.0033 (VBE 600) where VBE is in mV and the TC is in mV/°C. The accuracy of this TC is typically  $\pm$  0.01 mV/°C.
- 5. For maximum temperature accuracy, IC should not exceed 2 mA. See Figure 1.

## TYPICAL ELECTRICAL CHARACTERISTICS

# FIGURE 1 – BASE-EMITTER VOLTAGE versus COLLECTOR-EMITTER CURRENT



# FIGURE 2 — TEMPERATURE COEFFICIENT versus BASE-EMITTER VOLTAGE



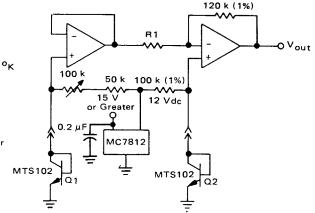


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## FIGURE 3 - ABSOLUTE TEMPERATURE MEASUREMENT

#### MTS102 MTS103 MTS103 MTS105 MTS105 MC7812 
NOTE: With Q1 at a known temperature, adjust  $R_{CAL}$  to set output voltage to  $V_{out}$  = TEMP x 10 mV. Output of MTS102, 3, 5 is then converted to  $V_{out}$  = 10 mV/ $^{0}$  - ( $^{0}$ F,  $^{0}$ C, or  $^{0}$ K)

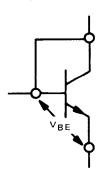
#### FIGURE 4 - DIFFERENTIAL TEMPERATURE MEASUREMENT



NOTE: With Q1 and Q2 at identical temperature, adjust RCAL for Vout = 0.000 V

#### **APPLICATIONS INFORMATION**

The base and collector leads of the device should be connected together in the operating circuit (pins 2 and 3). They are not internally connected.



The following example describes how to determine the  $V_{BE}$  versus temperature relationship for a typical shipment of various  $V_{BE}$  groups.

## **EXAMPLE**:

Given — Customer receives a shipment of MTS102 devices. The shipment consists of three groups of different nominal VBE values.

Group 1: VBE (nom) = 600 mV

Group 2: VBE (nom) = 580 mV

Group 3: VBE (nom) = 620 mV

Find - VBE versus Temperature Relationship.

1. Determine value of TC:

a. If VBE (nom) = 600 mV, TC = -2.25 mV/°C from the Electrical Characteristics table.

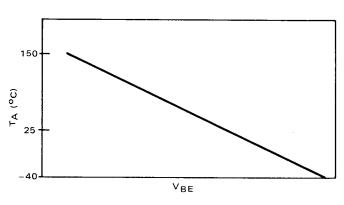
b. If VBE (nom) is less than or greater than 600 mV determine TC from the relationship described in Note 4.

(1)  $TC = -2.25 + 0.0033 (V_{BE} - 600)$  or see Figure 2.

2. Determine the VBE value at the extremes,  $-40^{\circ}$ C and  $+150^{\circ}$ C:

(2)  $V_{BE(T_A)} = V_{BE(25^{\circ}C)} + (TC)(T_A - 25^{\circ}C)$ where  $V_{BE(T_A)} =$  value of  $V_{BE}$  at desired temperature.

3. Plot the VBE versus TA curve using two VBE values: VBE(-40°C), VBE(25°C), or VBE(+150°C).



4. Given any measured VBE, the value of TA (to the accuracy value specified: MTS102 –  $\pm 2^{o}$ C, MTS103 –  $\pm 3^{o}$ C, MTS105 –  $\pm 5^{o}$ C) can be read from the above curve, or calculated from equation 2.



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## GROUP 1: VBE (nom) = 600 mV = VBE(25°C)

From the Electrical Characteristics table:

- 1.  $TC = -2.25 \text{ mV/}^{\circ}\text{C}$  for  $V_{BE} = 600 \text{ mV}$
- 2.  $V_{BE(150^{\circ}C)} = V_{BE(@25^{\circ}C)} + (TC)(150 25)$ = 600 + (-2.25)(125)
  - = 600 281.25
  - = 318.75 mV
- 3. The calibration curve for any device randomly selected from this group with  $V_{BE}$  (nom) = 600 mV is shown below.

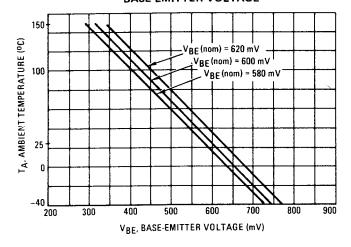
## GROUP 2: VBE (nom) = 580 mV = VBE(25°C)

- 1.  $TC = -2.25 + 0.0033(V_{BE} 600)$ 
  - = -2.25 + 0.0033(580 600)
  - = -2.25 0.066
  - = -2.316
- 2.  $V_{BE(150^{\circ}C)} = V_{BE(25^{\circ}C)} + TC(T_{A} 25^{\circ}C)$ 
  - = 580 + (-2.316)(150 25)
  - = 580 + (-2.316)(125)
  - = 290.5 mV
- The calibration curve for any device randomly selected from this group with VBE (nom) = 580 mV is shown below.

## GROUP 3: $V_{BE}$ (nom) = 620 mV = $V_{BE}$ (25°C)

- 1.  $TC = -2.25 + 0.0033(V_{BE} 600)$ 
  - = -2.25 + 0.0033(620 600)
  - = -2.184
- 2.  $V_{BE(150^{\circ}C)} = V_{BE(25^{\circ}C)} + (TC)(T_{A} 25^{\circ}C)$ 
  - = 620 + (-2.184)(150 25)
  - = 347 mV
- The calibration curve for any device randomly selected from this group with VBE (nom) = 620 mV is shown below.

# FIGURE 5 — AMBIENT TEMPERATURE versus BASE-EMITTER VOLTAGE





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